



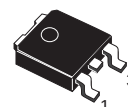
STGD3NB60HD

N-CHANNEL 6A - 600V - DPAK

PowerMESH™ IGBT

TYPE	V _{CES}	V _{CE(sat)} (Max) @25°C	I _C @100°C
STGD3NB60HD	600 V	< 2.8 V	6 A

- HIGH INPUT IMPEDANCE
- OFF LOSSES INCLUDE TAIL CURRENT
- LOW GATE CHARGE
- HIGH FREQUENCY OPERATION
- TYPICAL SHORT CIRCUIT WITHSTAND TIME
5micro S-family, 4 micro H family
- CO-PACKAGED WITH TURBOSWITCH™
ANTIPARALLEL DIODE



DPAK

DESCRIPTION

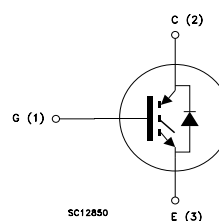
Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances.

The suffix "H" identifies a family optimized for high frequency applications (up to 50kHz) in order to achieve very high switching performances (reduced t_{fall}) maintaining a low voltage drop.

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS and PFC IN BOTH HARD SWITCH AND
RESONANT TOPOLOGIES

INTERNAL SCHEMATIC DIAGRAM



ORDERING INFORMATION

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGD3NB60HDT4	GD3NB60HD	DPAK	TAPE & REEL

STGD3NB60HD**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage ($V_{GS} = 0$)	600	V
V_{ECR}	Emitter-Collector Voltage	20	V
V_{GE}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current (continuous) at $T_C = 25^\circ\text{C}$	10	A
I_C	Collector Current (continuous) at $T_C = 100^\circ\text{C}$	6	A
$I_{CM} (\blacksquare)$	Collector Current (pulsed)	24	A
P_{TOT}	Total Dissipation at $T_C = 25^\circ\text{C}$	50	W
	Derating Factor	0.4	W/ $^\circ\text{C}$
T_{stg}	Storage Temperature	-55 to 150	$^\circ\text{C}$
T_j	Operating Junction Temperature		

($\blacksquare$) Pulse width limited by safe operating area

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case Max	2.5	$^\circ\text{C/W}$
Rthj-amb	Thermal Resistance Junction-ambient Max	100	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS ($T_{CASE} = 25^\circ\text{C}$ UNLESS OTHERWISE SPECIFIED)

OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{BR(CES)}$	Collector-Emitter Breakdown Voltage	$I_C = 250\ \mu\text{A}$, $V_{GE} = 0$	600			V
I_{CES}	Collector cut-off ($V_{GE} = 0$)	$V_{CE} = \text{Max Rating}$, $T_C = 25^\circ\text{C}$ $V_{CE} = \text{Max Rating}$, $T_C = 125^\circ\text{C}$			50 100	μA μA
I_{GES}	Gate-Emitter Leakage Current ($V_{CE} = 0$)	$V_{GE} = \pm 20\text{V}$, $V_{CE} = 0$			± 100	nA

ON (1)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{GE(th)}$	Gate Threshold Voltage	$V_{CE} = V_{GE}$, $I_C = 250\ \mu\text{A}$	3		5	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$V_{GE} = 15\text{V}$, $I_C = 3\ \text{A}$ $V_{GE} = 15\text{V}$, $I_C = 3\ \text{A}$, $T_j = 125^\circ\text{C}$		2.4 1.9	2.8	V V

ELECTRICAL CHARACTERISTICS (CONTINUED)

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g_{fs}	Forward Transconductance	$V_{CE} = 25\text{ V}$, $I_C = 3\text{ A}$		2.4		S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$		235 33 6.6		pF pF pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 480\text{ V}$, $I_C = 3\text{ A}$, $V_{GE} = 15\text{ V}$		21 6 7.6	27	nC nC nC
I_{CL}	Latching Current	$V_{clamp} = 480\text{ V}$, $T_j = 125^\circ\text{C}$ $R_G = 10\ \Omega$	12			A

SWITCHING ON

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Delay Time Rise Time	$V_{CC} = 480\text{ V}$, $I_C = 3\text{ A}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$		5 11		ns ns
$(di/dt)_{on}$ E_{on}	Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 480\text{ V}$, $I_C = 3\text{ A}$, $R_G = 10\ \Omega$ $V_{GE} = 15\text{ V}$, $T_j = 125^\circ\text{C}$		400 77		A/ μs μJ

SWITCHING OFF

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
t_c $t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off(**)}$ E_{ts}	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480\text{ V}$, $I_C = 3\text{ A}$, $R_{GE} = 10\ \Omega$, $V_{GE} = 15\text{ V}$		76 36 53 77 33 100		ns ns ns ns μJ μJ
t_c $t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off(**)}$ E_{ts}	Cross-over Time Off Voltage Rise Time Delay Time Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 480\text{ V}$, $I_C = 3\text{ A}$, $R_{GE} = 10\ \Omega$, $V_{GE} = 15\text{ V}$ $T_j = 125^\circ\text{C}$		180 82 58 110 88 165		ns ns ns ns μJ μJ

Note: 1. Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.

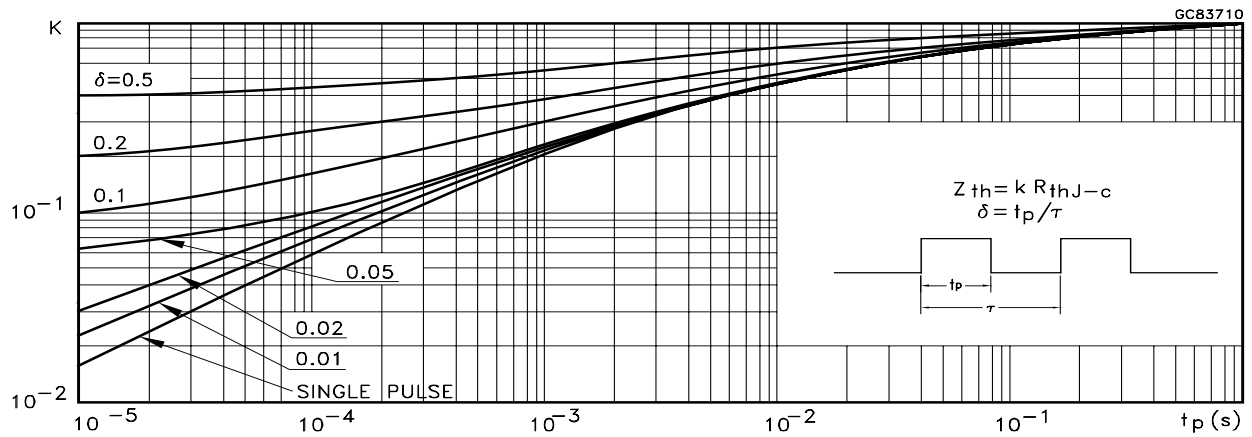
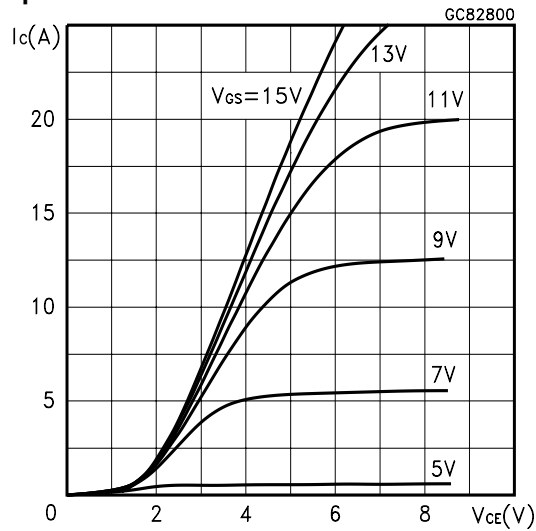
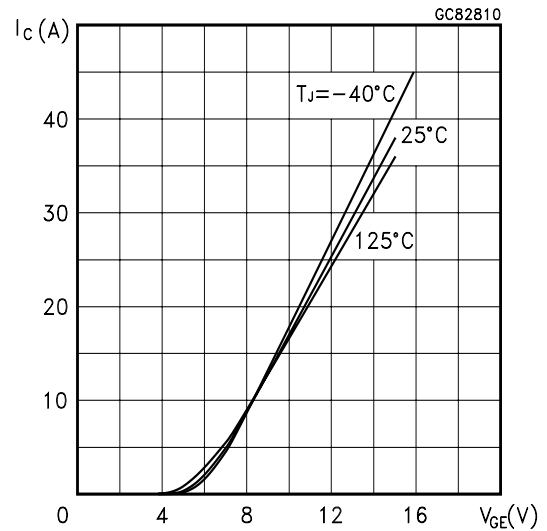
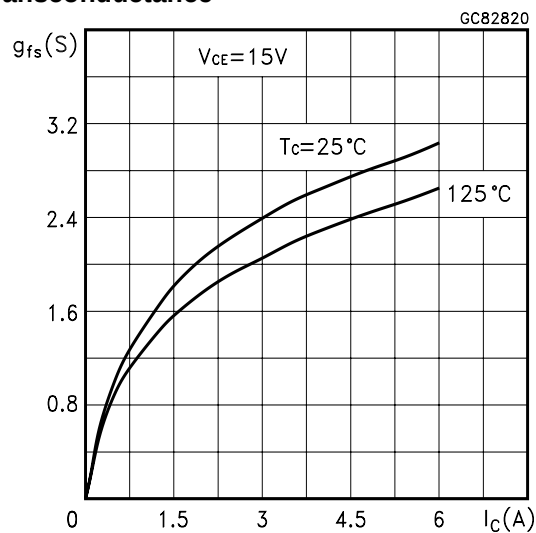
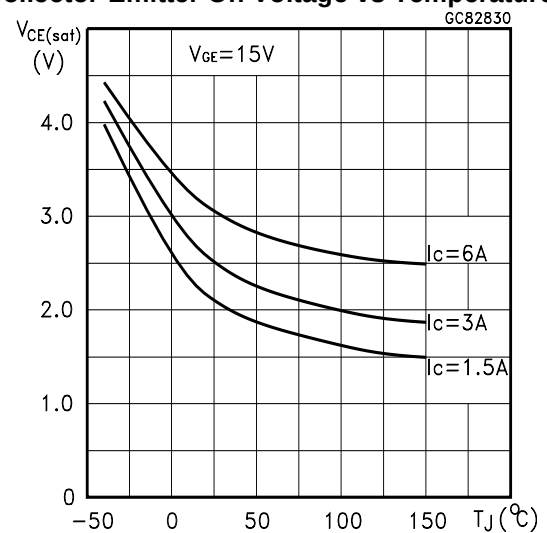
2. Pulse width limited by max. junction temperature.

(**) Losses include Also the Tail (Jedec Standardization)

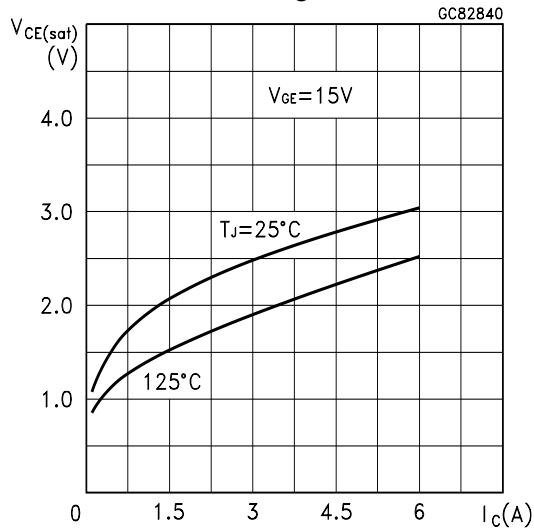
COLLECTOR-EMITTER DIODE

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_f I_{fm}	Forward Current Forward Current pulsed				1.5 12	A A
V_f	Forward On-Voltage	$I_f = 1.5\text{ A}$ $I_f = 1.5\text{ A}$, $T_j = 125^\circ\text{C}$		1.6 1.3	2.1	V V
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 1.5\text{ A}$, $V_R = 400\text{ V}$, $T_j = 125^\circ\text{C}$, $di/dt = 100\text{ A}/\mu\text{s}$		95 110 2.7		ns nC A

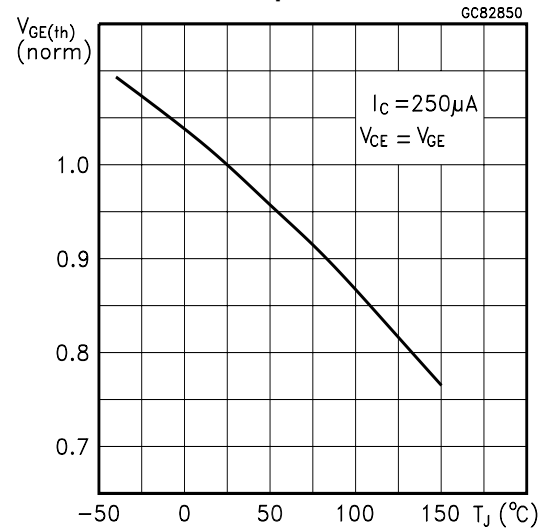


STGD3NB60HD**Thermal Impedance****Output Characteristics****Transfer Characteristics****Transconductance****Collector-Emitter On Voltage vs Temperature**

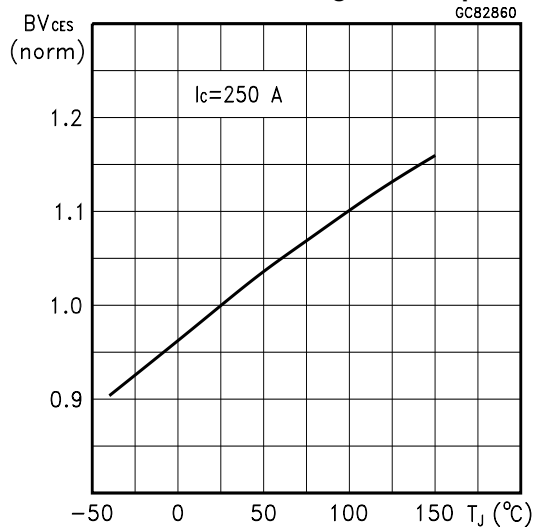
Collector-Emitter On Voltage vs Collector Current



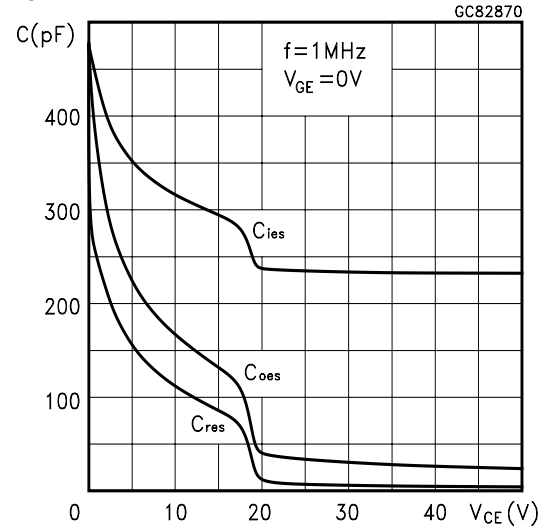
Gate Threshold vs Temperature



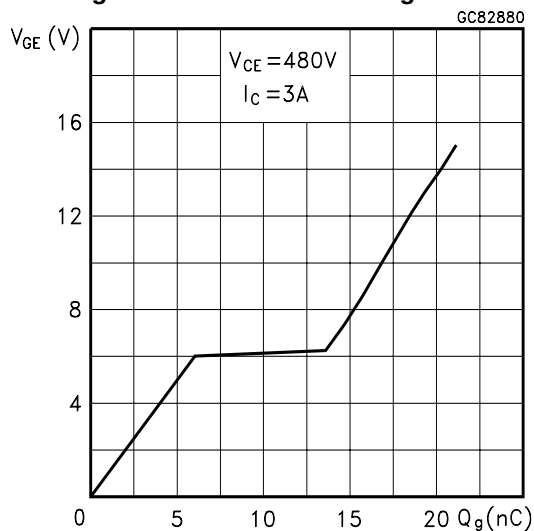
Normalized Breakdown Voltage vs Temperature



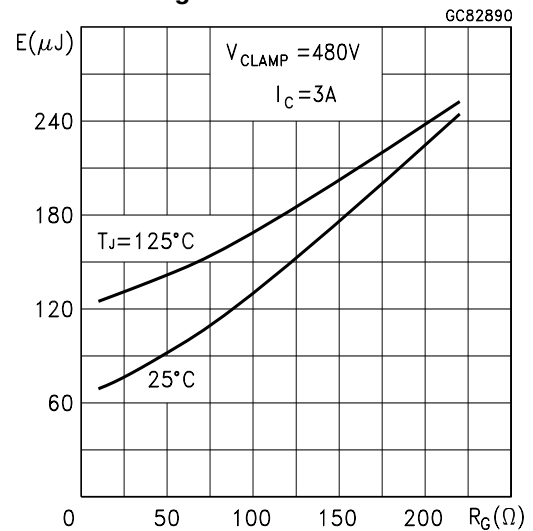
Capacitance Variations



Gate Charge vs Gate-Emmitter Voltage

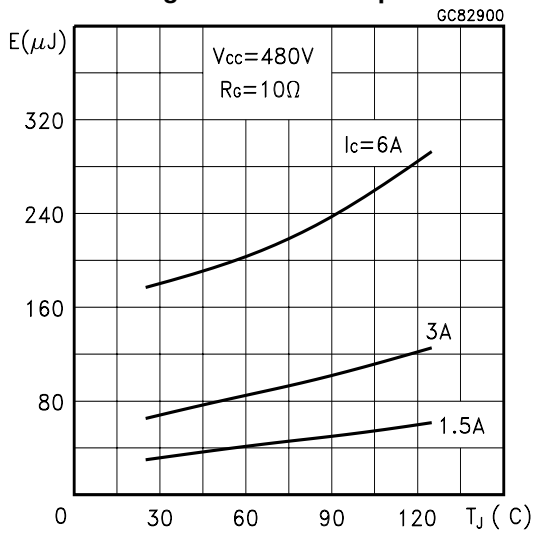


Total Switching Losses vs Gate Resistance

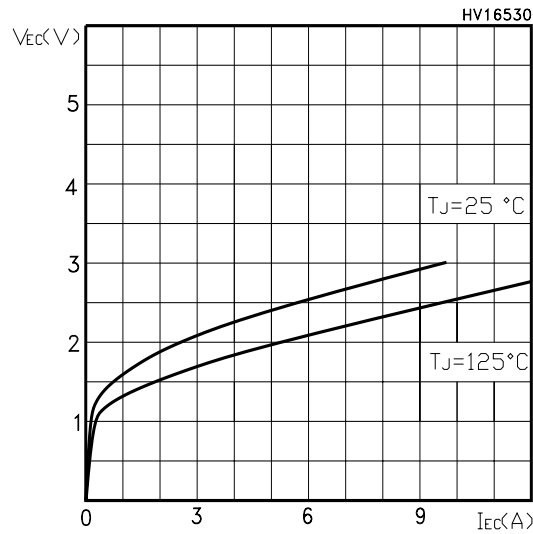


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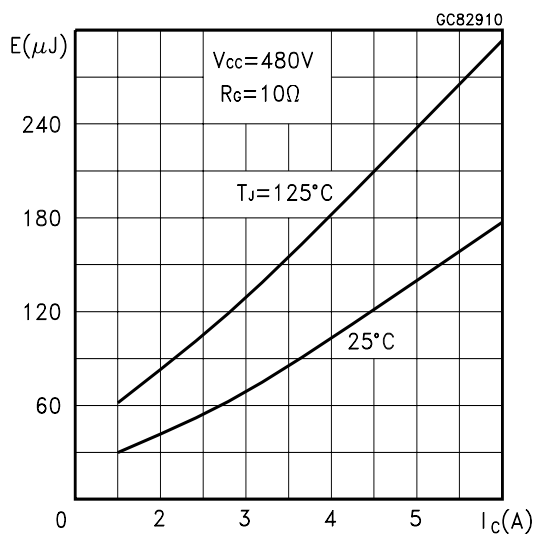
Total Switching Losses vs Temperature



Emitter-collector Diode Characteristics



Total Switching Losses vs Collector Current



Switching Off Safe Operating Area

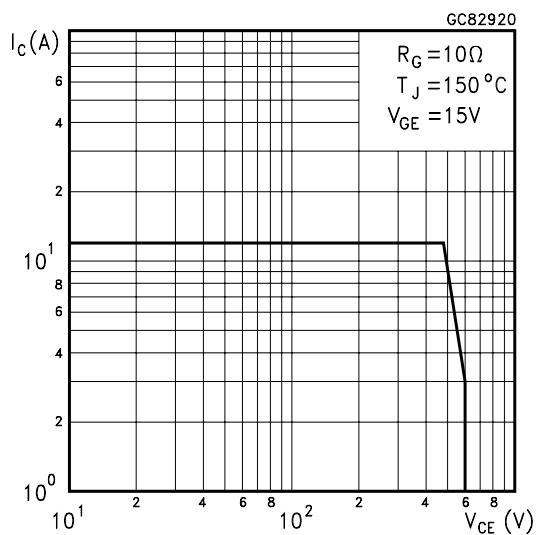
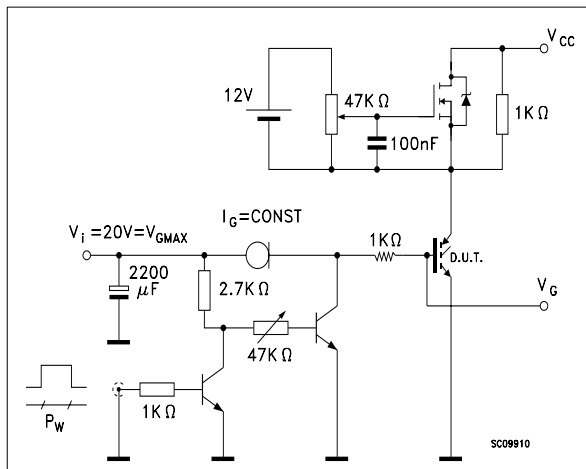
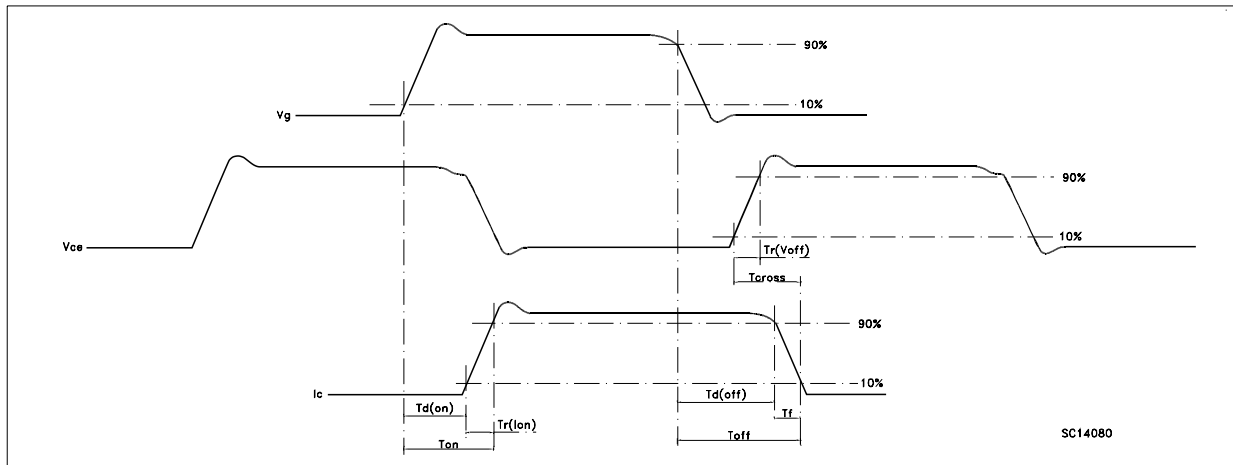
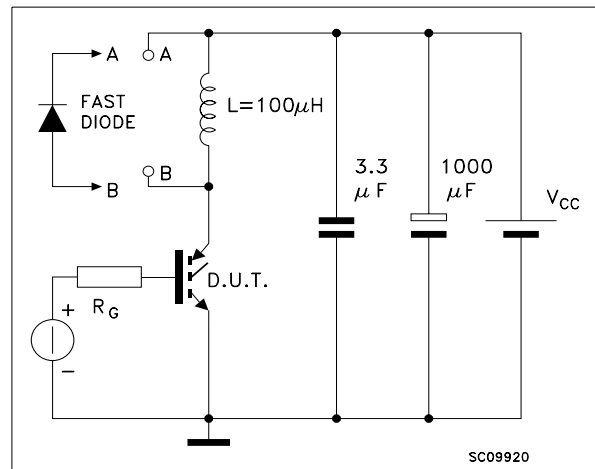
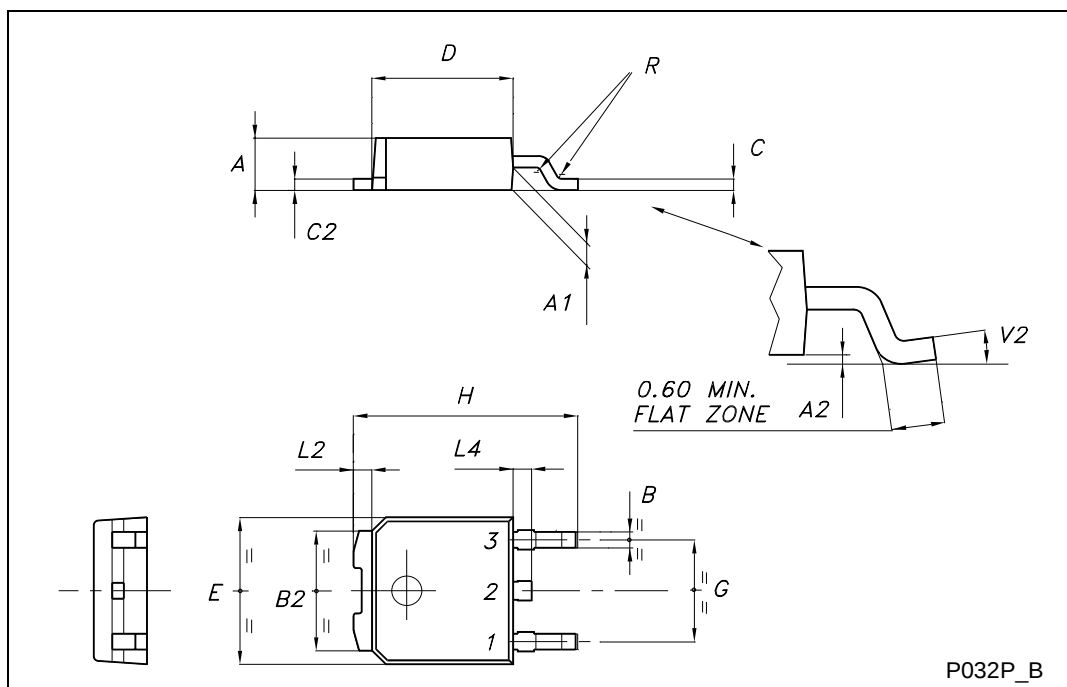


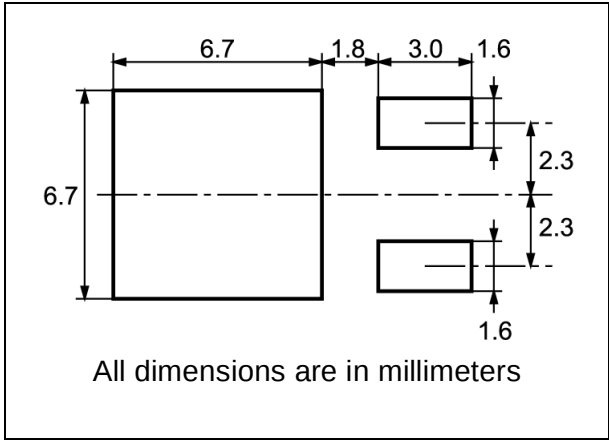
Fig. 1: Gate Charge test Circuit**Fig. 2: Test Circuit For Inductive Load Switching**

STGD3NB60HD**TO-252 (DPAK) MECHANICAL DATA**

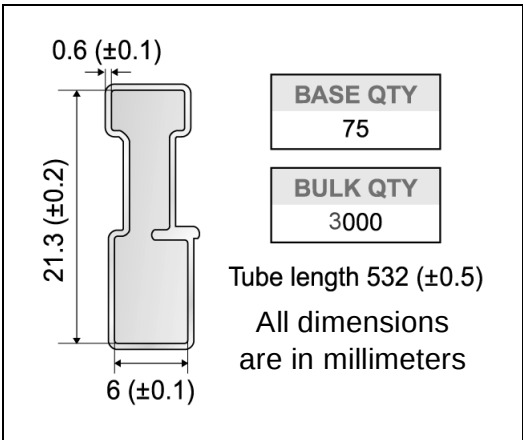
DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	2.20		2.40	0.087		0.094
A1	0.90		1.10	0.035		0.043
A2	0.03		0.23	0.001		0.009
B	0.64		0.90	0.025		0.035
B2	5.20		5.40	0.204		0.213
C	0.45		0.60	0.018		0.024
C2	0.48		0.60	0.019		0.024
D	6.00		6.20	0.236		0.244
E	6.40		6.60	0.252		0.260
G	4.40		4.60	0.173		0.181
H	9.35		10.10	0.368		0.398
L2		0.8			0.031	
L4	0.60		1.00	0.024		0.039
V2	0°		8°	0°		0°



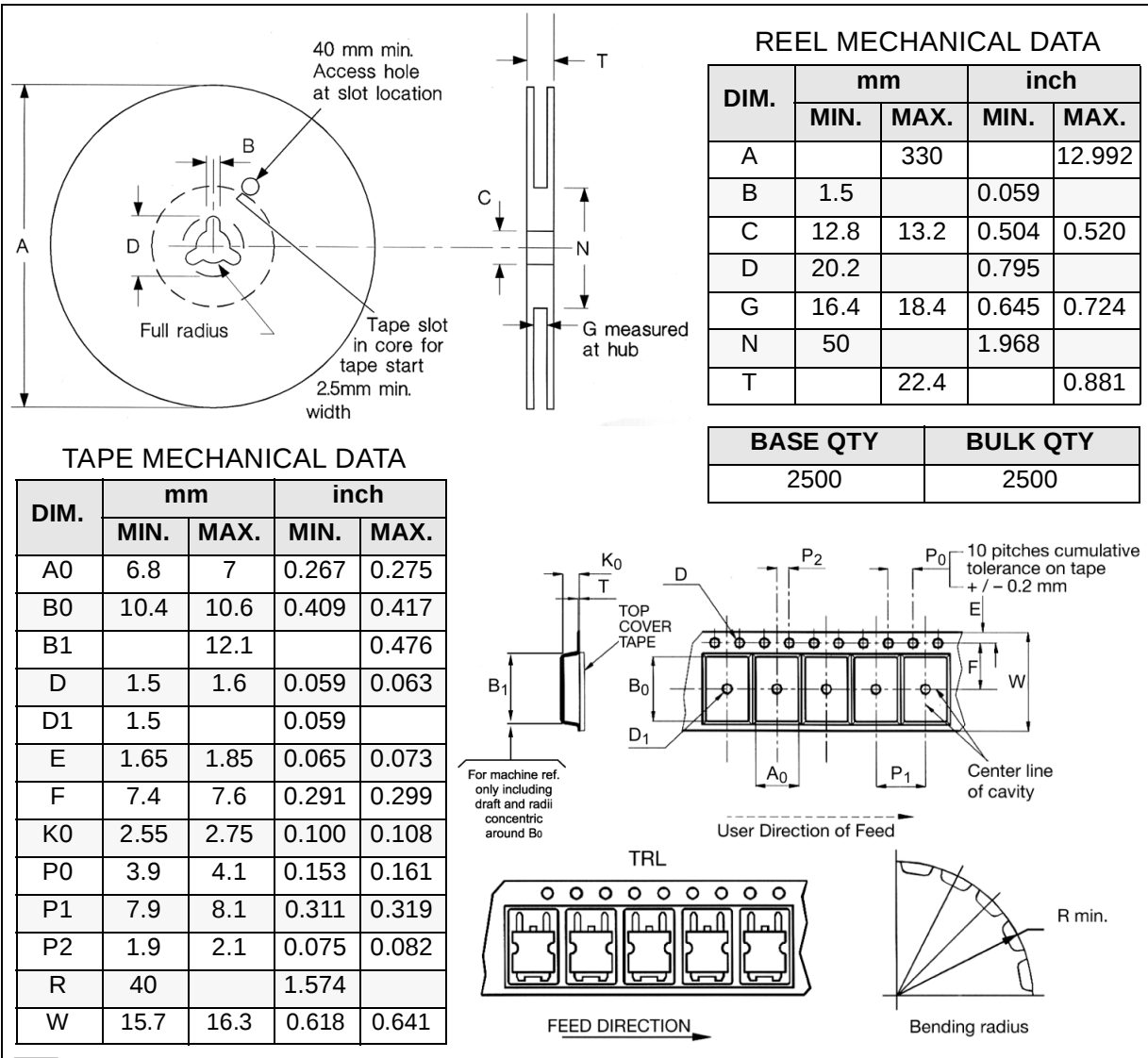
DPAK FOOTPRINT



TUBE SHIPMENT (no suffix)*



TAPE AND REEL SHIPMENT (suffix "T4")*



STGD3NB60HD

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